## NSN 5962-01-158-5206

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## **Body Length:** 1.290 inches **Body Width:** Between 0.500 inches and 0.610 inches **Body Height:** 0.210 inches **Maximum Power Dissipation Rating:** 1.02 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Hermetically sealed and monolithic and schottky and bipolar and programmed and positive outputs **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 13 input **Case Outline Source And Designator:** D-3 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: 5.5 volts power source **Time Rating Per Chacteristic:** 90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level output Memory Device Type: Rom **Special Features:** Alter in accordance w/g.E. Drawing 77a102342p1 **Test Data Document:** 81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 24 printed circuit

**Specification Data:** 

81349-mil-m-38510/208/usaf/ government specification

## Shelf Life:

NI/o

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Unit Of Measure:

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Demilitarization:

Yes - demil/mli

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